MAGNETORESISTANCE EFFECT ELEMENT[32]

ABSTRACT OF THE DISCLOSURE

A magnetoresistance effect element provided with a spin valve film composed of a first magnetic layer formed on a metallic buffer layer, a middle non-magnetic layer formed on the first magnetic layer, and a second magnetic layer formed on the non-magnetic layer, has an atomic-diffusion barrier layer whose average thickness is 2 nm or less formed in the interface between the metallic buffer layer and the first magnetic layer. Or a magnetoresistance effect element provided with a spin valve film composed of a first magnetic layer composed of a laminated film of a magnetic undercoat layer and a ferromagnetic layer, a middle non-magnetic layer formed on the first magnetic layer, and a second magnetic layer formed on the middle non-magnetic layer, has an atomic-diffusion barrier layer whose average thickness is 2 nm or less formed in the interface between the magnetic undercoat layer and the ferromagnetic layer.

FIGURE 1